

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

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Product data sheet

1. General description

High voltage high speed planar passivated NPN power switching transistor in a SOT428 (DPAK) surface mountable plastic package.

2. Features and benefits

- Fast switching
- · Low thermal resistance
- Surface mountable package
- · Tight DC gain spreads
- Very high voltage capability
- · Very low switching and conduction losses

3. Applications

- DC-to-DC converters
- · High frequency electronic lighting ballasts
- Inverters
- Motor control systems

4. Pinning information

Table 1. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	С
2	С	collector[1]		в
3	Е	emitter	<u> </u>	
mb	С	mounting base; connected to collector	1 3 DPAK (SOT428)	Ë sym123

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

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NPN power transistor

5. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
BUJ303CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

6. Marking

Table 3. Marking codes

Type number	Marking code
BUJ303CD	BUJ303CD

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mir	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	1050	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
Ic	collector current	Fig. 1; Fig. 2; Fig. 3	-	5	Α
I _{CM}	peak collector current		-	10	Α
I_{B}	base current		-	2	Α
I _{BM}	peak base current		-	4	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; <u>Fig. 4</u>	-	80	W
T _{stg}	storage temperature		-65	150	°C
T _j	junction temperature		-	150	°C

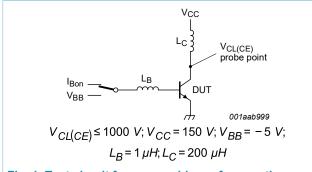


Fig. 1. Test circuit for reverse bias safe operating area

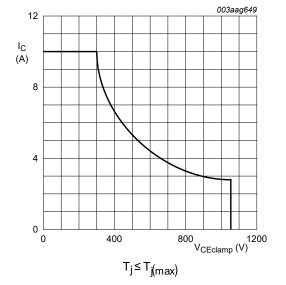
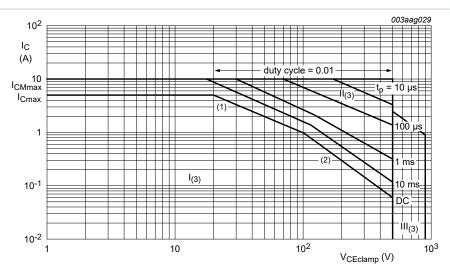


Fig. 2. Reverse bias safe operating area

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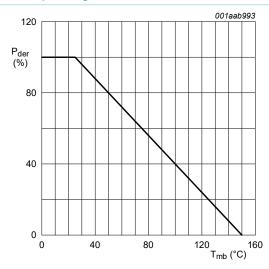
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- (1) P_{tot} maximum and P_{tot} peak maximum lines.
- (2) Second breakdown limits.
- (3) I = Region of permissible DC operation.
- II = Extension for repetitive pulse operation.
- III = Extension during turn-on in single transistor converters provided that $R_{BE} \le 100 \Omega$ and $t_p \le 0.6 \mu s$.

Fig. 3. Forward bias safe operating area for Tmb ≤ 25 °C



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig. 4. Normalized total power dissipation as a function of mounting base temperature

4 / 13

NPN power transistor

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint; Fig. 6	-	75	-	K/W

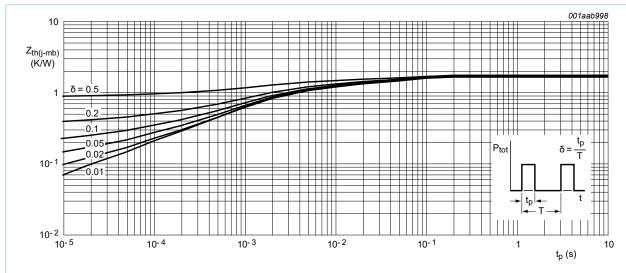


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

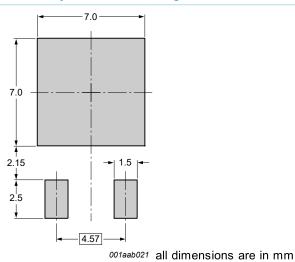


Fig. 6. Minimum footprint SOT428

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9. Characteristics

Table 6. Characteristics

	Parameter	Conditions		D.//:	Turn	Marc	Half
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara							
I _{CES}	collector-emitter cut-off current (base shorted)	V _{BE} = 0 V; V _{CE} = 1050 V	[1]	-	-	1	mA
	current (base shorted)	$V_{BE} = 0 \text{ V}; V_{CE} = 1050 \text{ V}; T_j = 125 ^{\circ}\text{C}$	[1]	-	-	2	mA
I _{CBO}	collector-base cut-off current (emitter open)	$V_{CB} = 1050 \text{ V}; I_{E} = 0 \text{ A}; T_{mb} = 25 \text{ °C}$	[1]	-	-	1	mA
I _{CEO}	collector-emitter cut-off current (base open)	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{mb} = 25 \text{ °C}$	[1]	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{mb} = 25 \text{ °C}$		-	-	0.1	mA
V_{CEOsus}	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 100 \text{ mA}; L_C = 25 \text{ mH};$ $T_{mb} = 25 ^{\circ}\text{C}; \text{Fig. 7}; \text{Fig. 8}$		400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 0.2 \text{ A}; T_{mb} = 25 \text{ °C}; Fig. 9; Fig. 10$		-	-	0.5	V
		$I_C = 3 \text{ A}; I_B = 1 \text{ A}; T_{mb} = 25 \text{ °C}; Fig. 9; Fig. 10}$		-	0.25	1.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3 \text{ A}; I_B = 1 \text{ A}; T_{mb} = 25 \text{ °C}; Fig. 11$		-	1	1.5	V
h _{FE}	DC current gain	I_C = 10 mA; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12		28	34	47	
		I_C = 250 mA; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12		35	43	57	
		I_C = 800 mA; V_{CE} = 3 V; T_{mb} = 25 °C; Fig. 12		31	37	48	
Dynamic ch	naracteristics (switching tir	nes - resistive load)					
t _{on}	turn-on time	I _C = 2.5 A; I _{Bon} = 0.5 A; I _{Boff} = -1 A;		-	1	-	ms
t _s	storage time	$R_L = 100 \Omega; T_j = 25 °C; Fig. 13; Fig. 14$		-	2.5	-	ms
t _f	fall time			-	0.3	-	ms
Dynamic ch	naracteristics (switching tir	mes - inductive load)				1	
t _s	storage time	$I_C = 2.5 \text{ A}; I_{Bon} = 0.5 \text{ A}; V_{BB} = -5 \text{ V};$ $L_B = 1 \mu\text{H}; T_j = 25 \text{ °C}; Fig. 15; Fig. 16$		-	2	-	ms
		I _C = 2.5 A; I _{Bon} = 0.5 A; V _{BB} = -5 V; L _B = 1 μH; T _j = 100 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	3	-	ms
t _f	fall time	I _C = 2.5 A; I _{Bon} = 0.5 A; V _{BB} = -5 V; L _B = 1 μH; T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	200	-	ns
		I _C = 2.5 A; I _{Bon} = 0.5 A; V _{BB} = -5 V; L _B = 1 μH; T _i = 100 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	300	-	ns

^[1] Measured with half-sine wave voltage (curve tracer).

6 / 13

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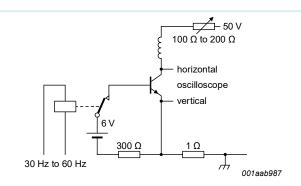


Fig. 7. Test circuit for collector-emitter sustaining voltage

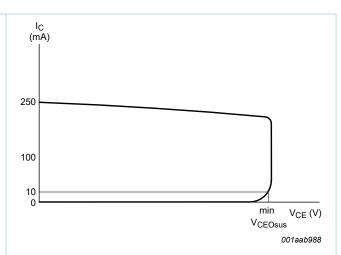


Fig. 8. Oscilloscope display for collector-emitter sustaining voltage test waveform

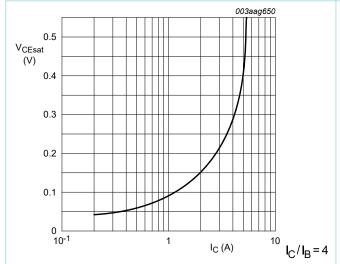


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

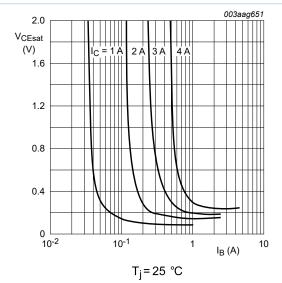


Fig. 10. Collector-emitter saturation voltage as a function of base current; typical values

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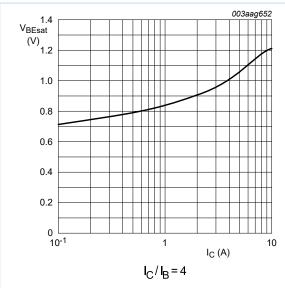


Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

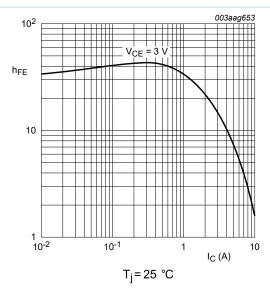
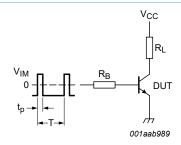


Fig. 12. DC current gain as a function of collector current; typical values



 V_{IM} = -6 to +8 V; V_{CC} = 250 V; t_p = 20 μ s; δ = $\frac{t_p}{T}$ = 0.01 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig. 13. Test circuit for resistive load switching

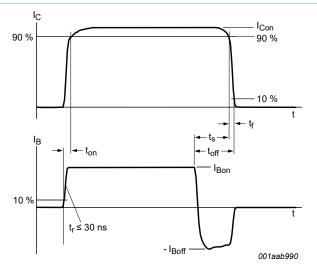
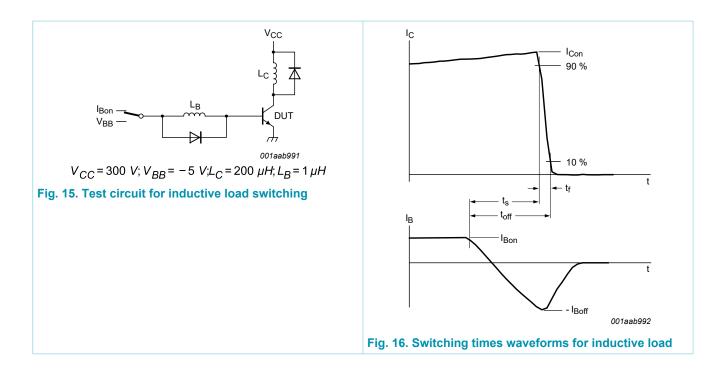


Fig. 14. Switching times waveforms for resistive load

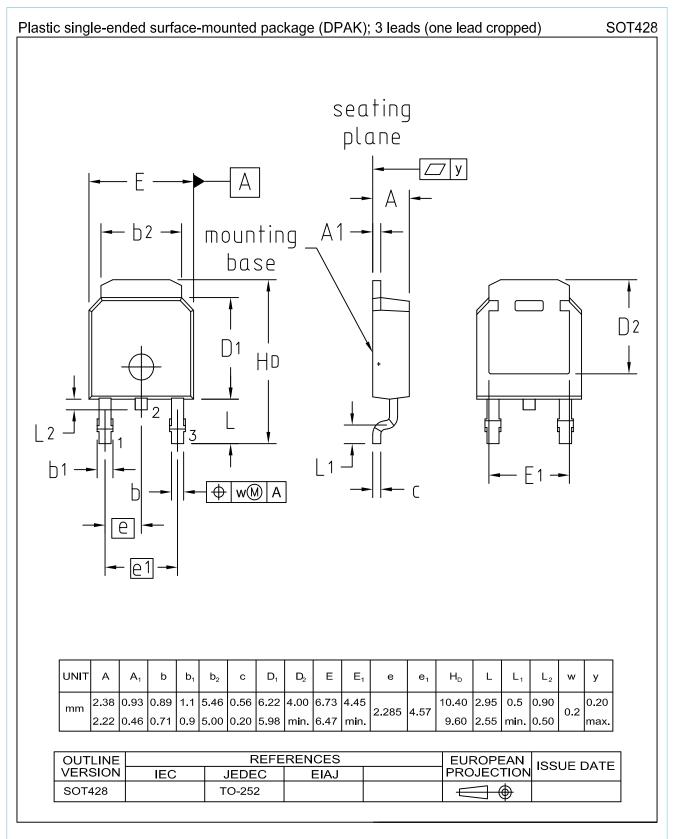
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9 / 13

10. Package outline



NPN power transistor

11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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BUJ303CD

NPN power transistor

12. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Pinning information	1
5.	Ordering information	2
6.	Marking	2
7.	Limiting values	3
8.	Thermal characteristics	
9.	Characteristics	6
10.	Package outline	10
11.	Legal information	11

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